

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	44	(250/492.24).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L2	0	(250/396).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L3	2210	(250/492.1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L4	706	(250/492.22).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L5	2741	(250/492.3).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L6	5257	I1 or I3 or I4 or I5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 14:49
L7	27	pyroelectric near1 emit\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:07
L8	10	I7 and ((substrate or wafer or semiconductor) near3 (hold\$3 or stage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:13

L9	8	I8 and dielectric\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L10	7	I9 and heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L11	7	I10 and magnet\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L12	2	I11 and (semiconduct\$4 near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:06
L13	5	I11 and I6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:06
L14	2	(method with (fabricat\$6 or manufatur\$4 or mak\$3) with (pyroelectric near1 emit\$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:09
L15	5	((fabricat\$6 or manufatur\$4 or mak\$3) with (pyroelectric near1 emit\$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:08
L16	2	(method with (fabricat\$6 or manufatur\$4 or mak\$3) with (pyroelectric near1 emit\$5))". \$clm."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:09

L17	1	((pyroelectric near1 emit\$5) with ((substrate or wafer or semiconductor) near3 (hold\$3 or stage)) with dielectric\$3 with heat\$3 with magnet\$4 with (semiconductor near2 film near4 dielectric\$4))".\$clm."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:17
L18	4	(pyroelectric near2 plate) and (pattern\$4 near2 (mask or reticle)) and ((prevent\$3 or block\$4) with electron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:50
L19	0	(making or fabricat\$4 or manufatur\$4) with (pyroelectric near2 plate) with (pattern\$4 near2 (mask or reticle)) with((prevent\$3 or block\$4) with electron))".\$clm."	US-PGPUB	OR	ON	2006/02/06 15:51